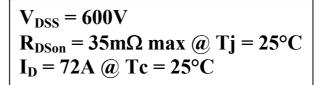
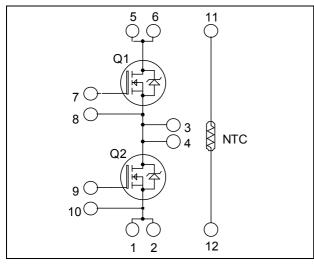
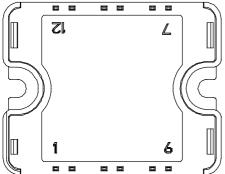


Phase leg Super Junction MOSFET Power Module







Pins 1/2; 3/4; 5/6 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

• COOLMOS

Power Semiconductors

- Ultra low R_{DSon}
- Low Miller capacitance
- Ultra low gate charge
- Avalanche energy rated
- Very rugged
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		600	V
Ţ	Continuous Drain Current	$T_c = 25^{\circ}C$	72	
I_D	Continuous Drain Current	$T_c = 80$ °C	54	A
I_{DM}	Pulsed Drain current		200	
V_{GS}	Gate - Source Voltage		±20	V
R _{DSon}	Drain - Source ON Resistance		35	mΩ
P_{D}	Maximum Power Dissipation $T_c = 25^{\circ}C$		416	W
I_{AR}	Avalanche current (repetitive and non repetitive)		20	A
E_{AR}	Repetitive Avalanche Energy		1	m I
E_{AS}	Single Pulse Avalanche Energy		1800	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 25^{\circ}C$			40	۸	
		$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 125^{\circ}C$			375	μΑ	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 72A$			35	mΩ	
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 5.4 \text{mA}$	2.1	3	3.9	V	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±150	nA	

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		14		
C_{oss}	Output Capacitance	$V_{\rm DS} = 25V$		5.13		nF
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		0.42		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		518		
Q_{gs}	Gate – Source Charge	$V_{\rm Bus} = 300 V$		58		nC
Q_{gd}	Gate – Drain Charge	$I_{D} = 72A$		222		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching @ 125°C		21		
$T_{\rm r}$	Rise Time	$V_{GS} = 15V$ $V_{Bus} = 400V$		30		na
$T_{d(off)}$	Turn-off Delay Time	$I_{\rm D} = 72A$		283		ns
T_{f}	Fall Time	$R_G = 2.5\Omega$		84		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		1340		T
E_{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		1960		μJ
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C		2192		1
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		2412		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source current		$Tc = 25^{\circ}C$		72		Α
	(Body diode)		$Tc = 80^{\circ}C$		54		Λ
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -72A$				1.2	V
dv/dt	Peak Diode Recovery •					6	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -72A$	$T_j = 25^{\circ}C$		580		ns
Qrr	Reverse Recovery Charge	$V_R = 350V$ $di_S/dt = 200A/\mu s$	$T_j = 25$ °C		46		μС

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq \text{- 72A} \qquad \text{di/dt} \leq 200 \text{A/} \mu \text{s} \qquad V_R \leq V_{DSS} \qquad T_j \leq 150 ^{\circ} \text{C}$



Thermal and package characteristics

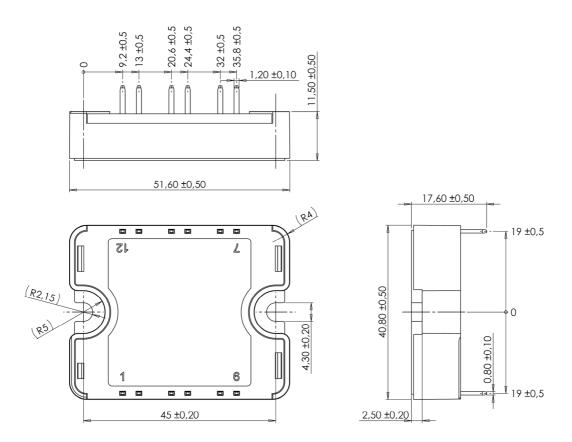
Symbol	Characteristic		Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance				0.3	°C/W	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
T_{J}	Operating junction temperature range		-40		150		
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight	_				80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature at T

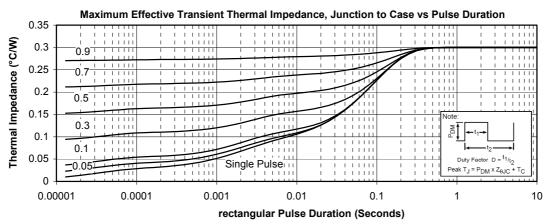
SP1 Package outline (dimensions in mm)

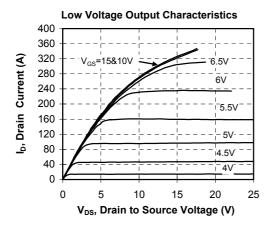


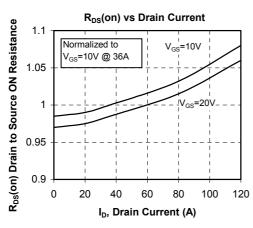
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

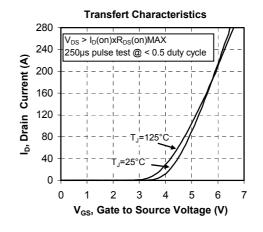


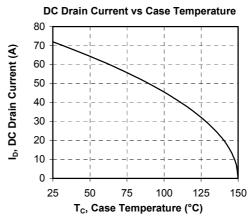
Typical Performance Curve



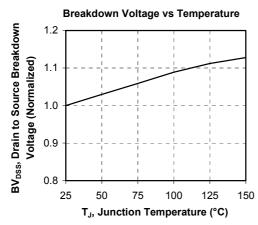


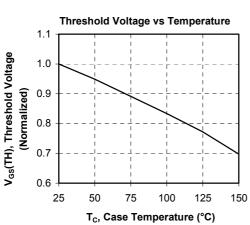


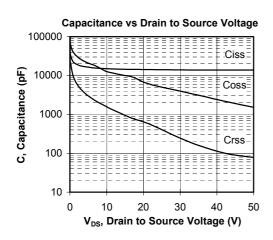


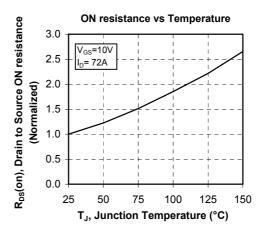


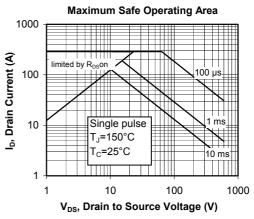


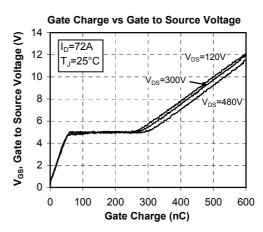




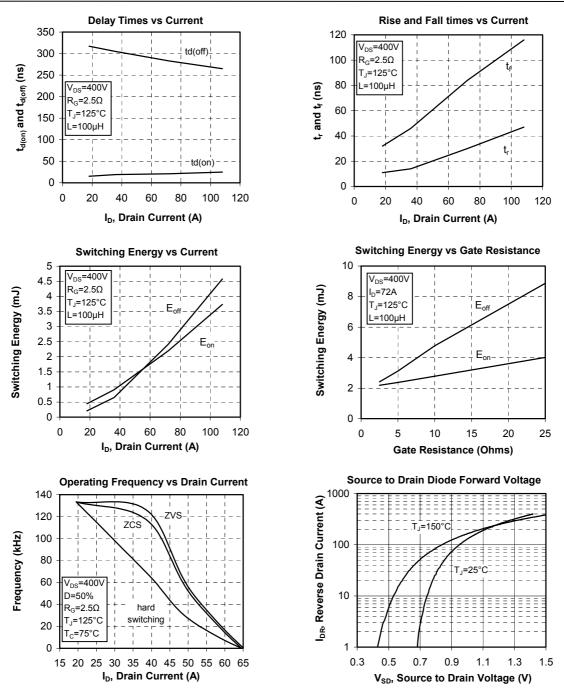












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